NIKO-SEM

N-Channel High Voltage Mode Field Effect Transistor

P2260WTF

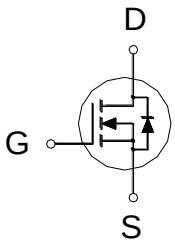
TO-220F

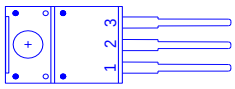
Halogen-Free & Lead-Free

RoHS Compliant

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
600V	175mΩ	22A





1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUN RATINGS(T_A=25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current[2,4]	T_C = 25 °C	I_D	22	A
	T_C = 100 °C		14	
Pulsed Drain Current[1]		I_{DM}	55	
Avalanche Current[3]		I_{AS}	2.9	A
Avalanche Energy[3]		E_{AS}	168	mJ
Power Dissipation	T_C = 25 °C	P_D	43	W
	T_C = 100 °C		17	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.3	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	°C / W

[1]Pulse width limited by maximum junction temperature.
[2]Ensure that the channel temperature does not exceed 150°C.
[3]V_{DD} = 50V , L = 40mH ,starting T_J = 25°C.
[4]Current limited by package.

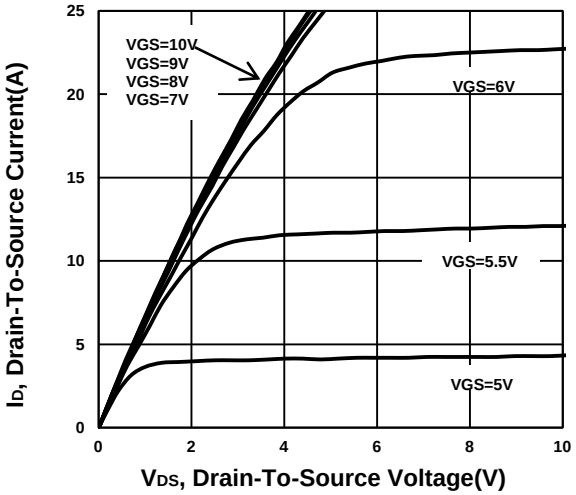
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	600			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3.4	4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±30V			±100	nA
Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600V, V_{GS} = 0V , T_C = 25 °C			1	μA
		V_{DS} = 480V, V_{GS} = 0V , T_C = 100 °C			100	

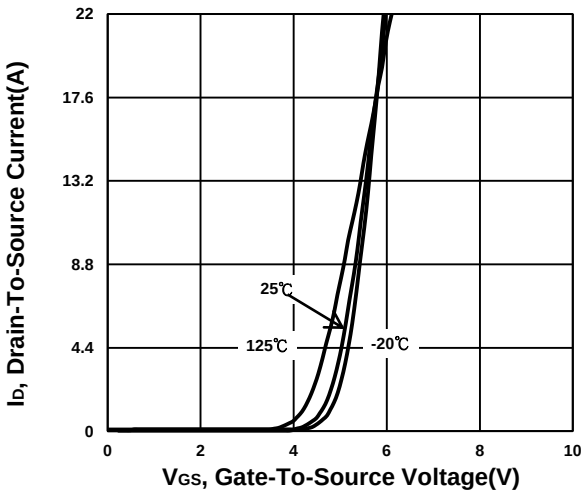
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 11A		150	175	mΩ
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 11A		19		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 100V, f = 250KHz		1358		pF
Output Capacitance	C_{oss}			56		
Reverse Transfer Capacitance	C_{rss}			7		
Effective Output Capacitance[4]	$C_{o(er)}$	V_{GS} = 0V, V_{DS} = 0 to 480V		55		
Gate Resistance	Rg	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		2.5		Ω
Total Gate Charge[2]	Q_g	V_{DD} = 480V, I_D =11A, V_{GS} = 10V		28		nC
Gate-Source Charge[2]	Q_{gs}			8.6		
Gate-Drain Charge[2]	Q_{gd}			8.2		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 300V, I_D =11A, R_G= 10Ω		31		nS
Rise Time[2]	t_r			44		
Turn-Off Delay Time[2]	$t_{d(off)}$			104		
Fall Time[2]	t_f			41		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				22	A
Forward Voltage[1]	V_{SD}	I_F =22A, V_{GS} = 0V			1.5	V
Reverse Recovery Time	t_{rr}	I_F =11A, dI_F/dt = 100A / μS		314		nS
Reverse Recovery Charge	Q_{rr}			3.8		uC

[1]Pulse test : Pulse Width ≤ 380 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.
[3]Pulse width limited by maximum junction temperature.
[4]$C_{o(er)}$ is a fixed capacitance that gives the same stored energy as Coss while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

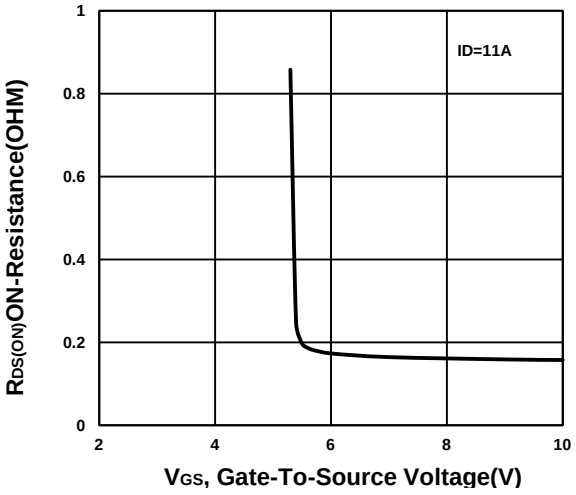
Output Characteristics



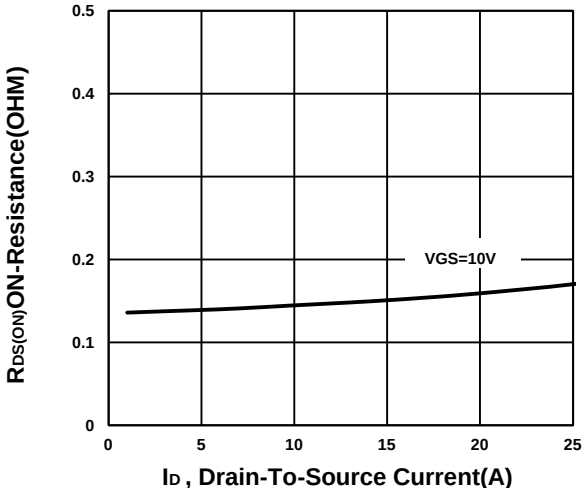
Transfer Characteristics



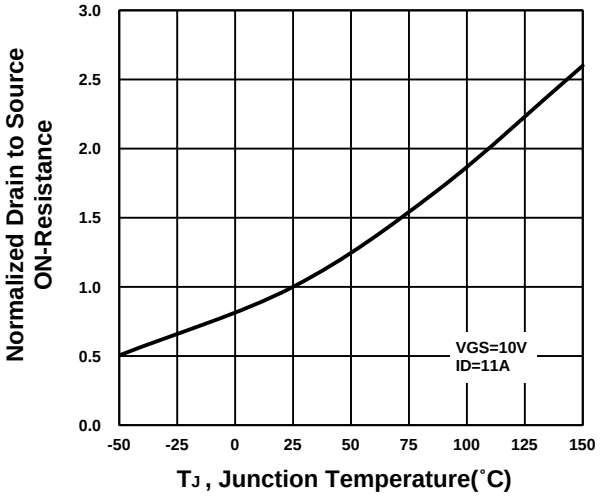
On-Resistance VS Gate-To-Source Voltage



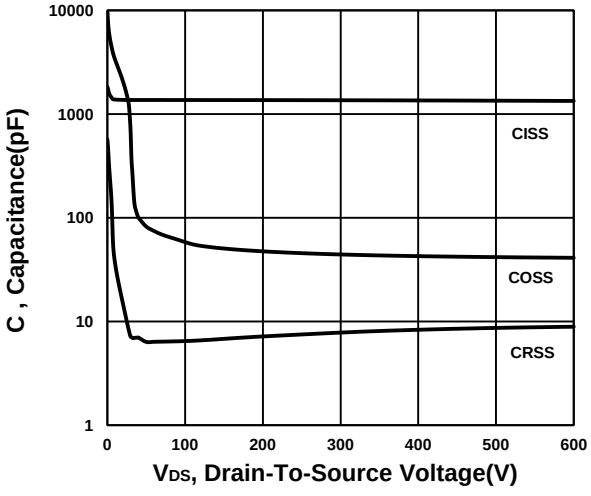
On-Resistance VS Drain Current



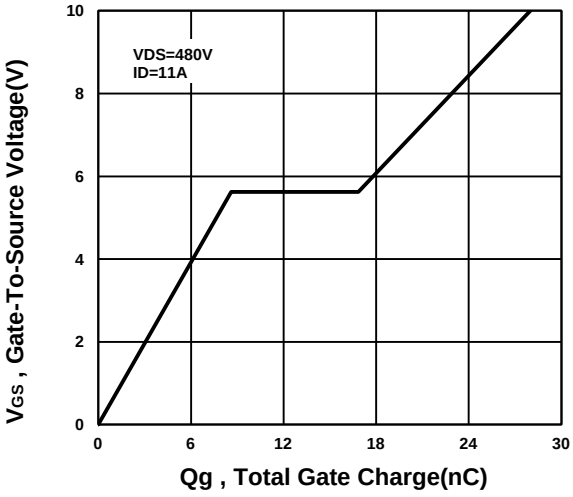
On-Resistance VS Temperature



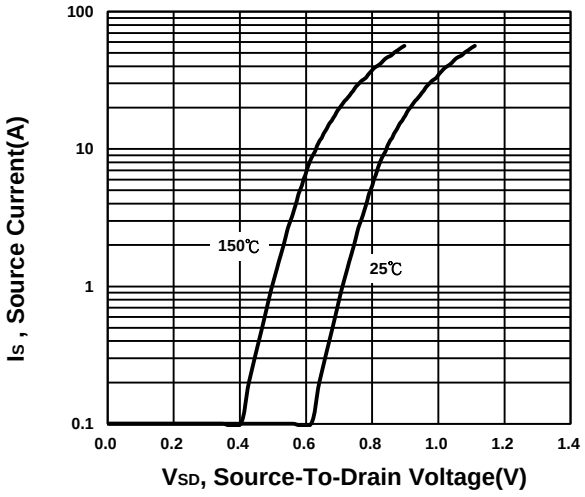
Capacitance Characteristic



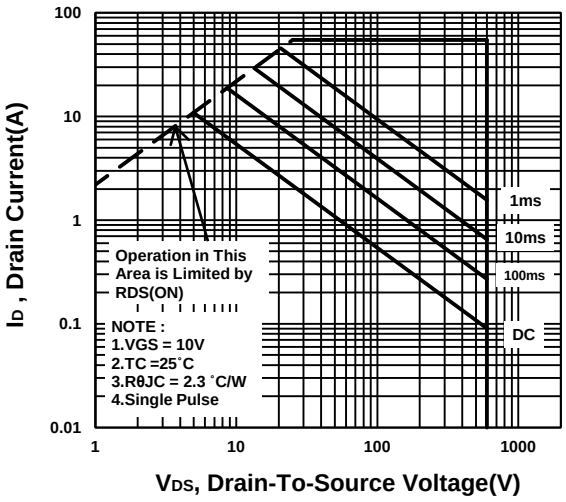
Gate charge Characteristics



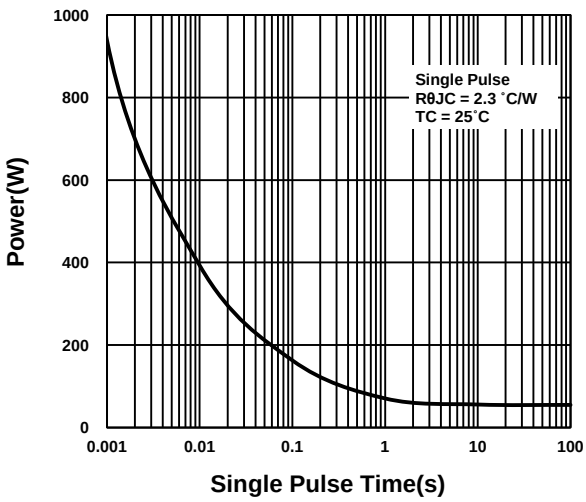
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve